

NX3DV2567

Low-ohmic four-pole double-throw analog switch

Rev. 2.1 — 4 October 2023

Product data sheet

1 General description

The NX3DV2567 is a four-pole double-throw analog switch (4PDT) optimized for switching WLAN-SIM supply, data and control signals. It has one digital select input (S) and four switches each with two independent input/outputs (nY0 and nY1) and a common input/output (nZ). Schmitt trigger action at S makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 1.4 V to 4.3 V.

A low input voltage threshold allows pin S to be driven by lower level logic signals without significant increase in supply current I_{CC} . This makes it possible for the NX3DV2567 to switch 4.3 V signals with a 1.8 V digital controller, eliminating the need for logic level translation.

The NX3DV2567 allows signals with amplitude up to V_{CC} to be transmitted from nZ to nY0 or nY1; or from nY0 or nY1 to nZ.

2 Features and benefits

- Wide supply voltage range from 1.4 V to 4.3 V
- Very low ON resistance for supply path:
 - 0.5 Ω (typical) at $V_{CC} = 1.8$ V
 - 0.45 Ω (typical) at $V_{CC} = 2.7$ V
- Low ON resistance for data path:
 - 7 Ω (typical) at $V_{CC} = 1.8$ V
 - 6 Ω (typical) at $V_{CC} = 2.7$ V
- Low ON capacitance for data path
- Wide -3 db bandwidth > 160 MHz
- Break-before-make switching
- High noise immunity
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 4000 V
 - HBM JESD22-A114F Class 3A I/O to GND exceeds 7000 V
 - CDM AEC-Q100-011 revision B exceeds 1000 V
- CMOS low-power consumption
- Latch-up performance exceeds 100 mA per JESD 78B Class II Level A
- 1.8 V control logic at $V_{CC} = 3.6$ V
- Control input accepts voltages above supply voltage
- Very low supply current, even when input is below V_{CC}
- High current handling capability (350 mA continuous current under 3.3 V supply for supply path switch)
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

3 Applications

- Cell phone, PDA, digital camera, printer and notebook
- LCD monitor, TV and set-top box



4 Ordering information

Table 1. Ordering information

Type number	Topside marking	Package		
		Name	Description	Version
NX3DV2567HR	D60	HXQFN16(U)	plastic thermal enhanced extremely thin quad flat package; no leads; 16 terminals; body 3 x 3 x 0.5 mm	SOT1039-2
NX3DV2567GU	D60	XQFN16	plastic, extremely thin quad flat package; no leads; 16 terminals; body 1.80 x 2.60 x 0.50 mm	SOT1161-1

4.1 Ordering options

Table 2. Ordering options

Type number	Orderable part number	Package	Packing method	Minimum order qty	Temperature
NX3DV2567HR	NX3DV2567HR,115	HXQFN16(U)	REEL 7" Q1/T1 NDP	1500	T _{amb} = -40 °C to +125 °C
NX3DV2567GU	NX3DV2567GU,115	XQFN16	REEL 7" Q1/T1 NDP	4000	T _{amb} = -40 °C to +125 °C

5 Functional diagram

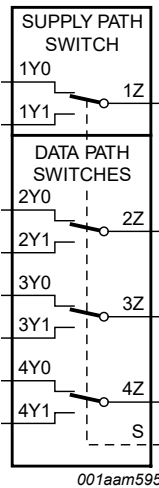


Figure 1. Logic symbol

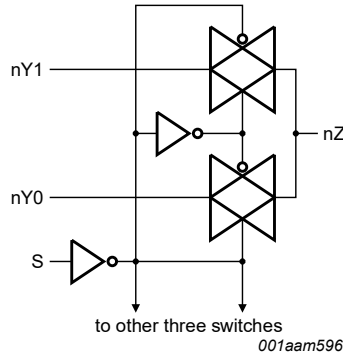


Figure 2. Logic diagram (one switch)

6 Pinning information

6.1 Pinning

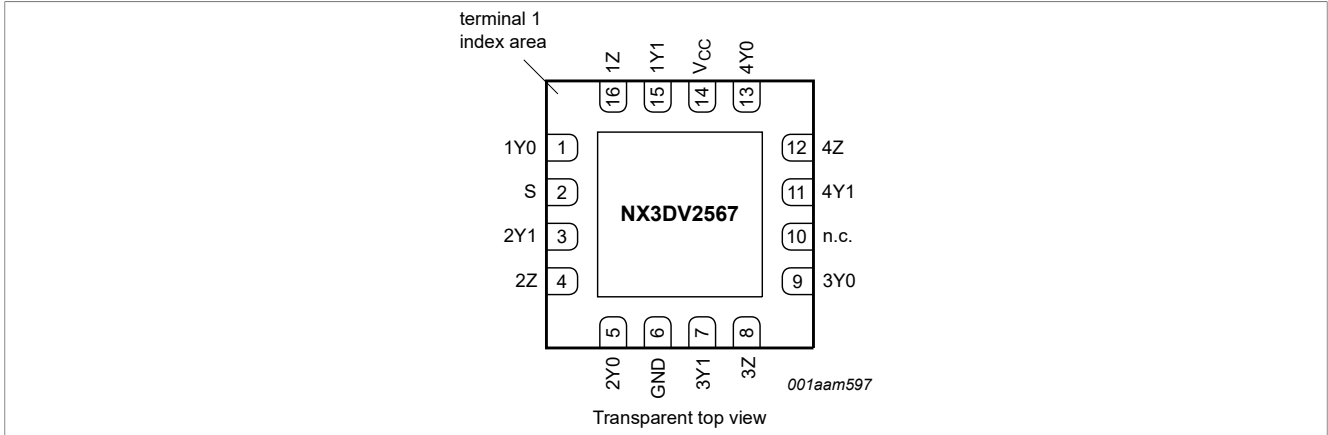


Figure 3. Pin configuration SOT1039-2 (HXQFN16(U))

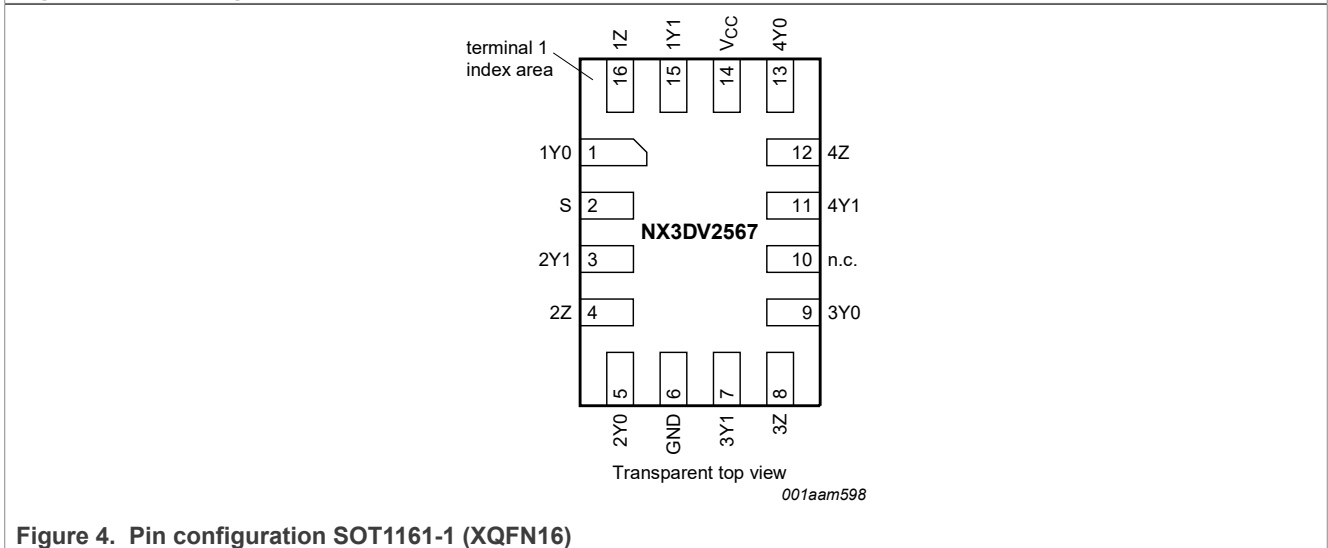


Figure 4. Pin configuration SOT1161-1 (XQFN16)

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1Y0	1	independent input or output (supply switch)
2Y0, 3Y0, 4Y0	5, 9, 13	independent input or output (data switch)
S	2	select input
1Y1	15	independent input or output (supply switch)
2Y1, 3Y1, 4Y1	3, 7, 11	independent input or output (data switch)
1Z	16	common output or input (supply switch)
2Z, 3Z, 4Z	4, 8, 12	common output or input (data switch)
GND	6	ground (0 V)

Table 3. Pin description...continued

Symbol	Pin	Description
n.c.	10	not connected
V _{CC}	14	supply voltage

7 Functional description

Table 4. Function table^[1]

Input S	Channel on
L	nY0
H	nY1

[1] H = HIGH voltage level; L = LOW voltage level.

8 Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
V _I	input voltage	select input S	^[1] -0.5	+4.6	V
V _{SW}	switch voltage		^[2] -0.5	V _{CC} + 0.5	V
I _{IK}	input clamping current	V _I < -0.5 V	-50	-	mA
I _{SK}	switch clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-	±50	mA
I _{SW}	switch current	supply path switch			
		V _{SW} > -0.5 V or V _{SW} < V _{CC} + 0.5 V; source or sink current	-	±350	mA
		V _{SW} > -0.5 V or V _{SW} < V _{CC} + 0.5 V; pulsed at 1 ms duration, < 10 % duty cycle; peak current	-	±500	mA
		data path switch			
		V _{SW} > -0.5 V or V _{SW} < V _{CC} + 0.5 V; source or sink current	-	±128	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	^[3] ^[4] -	250	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed but may not exceed 4.6 V.

[3] For HXQFN16(U) package: above 135 °C the value of P_{tot} derates linearly with 16.9 mW/K.

[4] For XQFN16 package: above 133 °C the value of P_{tot} derates linearly with 14.5 mW/K.

9 Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		1.4	4.3	V
V _I	input voltage	select input S	0	4.3	V
V _{SW}	switch voltage		^[1] 0	V _{CC}	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.4 V to 4.3 V	^[2] -	200	ns/V

[1] To avoid sinking GND current from terminal nZ when switch current flows in terminal nYn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal nZ, no GND current will flow from terminal nYn. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to control signal levels.

10 Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

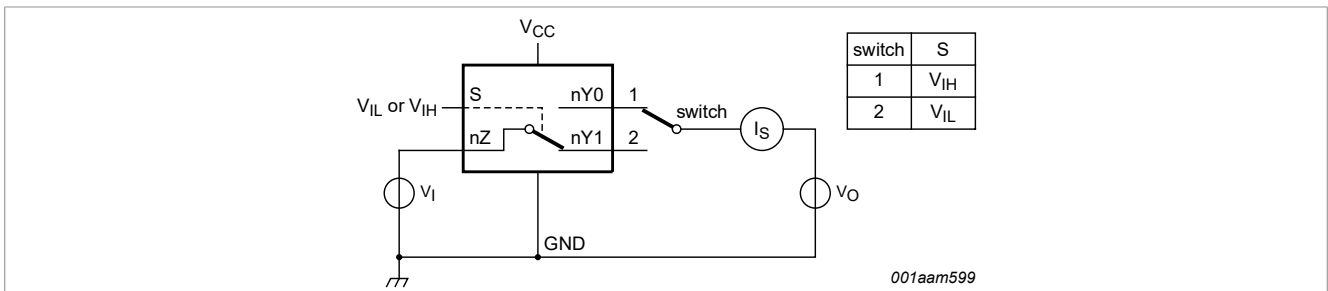
Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.4 V to 1.6 V	0.9	-	-	0.9	-	-	V
		V _{CC} = 1.65 V to 1.95 V	0.9	-	-	0.9	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.1	-	-	1.1	-	-	V
		V _{CC} = 2.7 V to 3.6 V	1.3	-	-	1.3	-	-	V
		V _{CC} = 3.6 V to 4.3 V	1.4	-	-	1.4	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.4 V to 1.6 V	-	-	0.3	-	0.3	0.3	V
		V _{CC} = 1.65 V to 1.95 V	-	-	0.4	-	0.4	0.3	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.4	-	0.4	0.4	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.5	-	0.5	0.5	V
		V _{CC} = 3.6 V to 4.3 V	-	-	0.6	-	0.6	0.6	V
I _I	input leakage current	select input S; V _I = GND to 4.3 V; V _{CC} = 1.4 V to 4.3 V	-	-	-	-	±0.5	±1	μA
I _{S(OFF)}	OFF-state leakage current	nY0 and nY1 port; see Figure 5							
		V _{CC} = 1.4 V to 3.6 V	-	-	±5	-	±50	±500	nA
		V _{CC} = 3.6 V to 4.3 V	-	-	±10	-	±50	±500	nA
I _{S(ON)}	ON-state leakage current	nZ port; V _{CC} = 1.4 V to 3.6 V; see Figure 6							
		V _{CC} = 1.4 V to 3.6 V	-	-	±5	-	±50	±500	nA
		V _{CC} = 3.6 V to 4.3 V	-	-	±10	-	±50	±500	nA
I _{CC}	supply current	V _I = V _{CC} or GND; V _{SW} = GND or V _{CC}							

Table 7. Static characteristics...continued

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

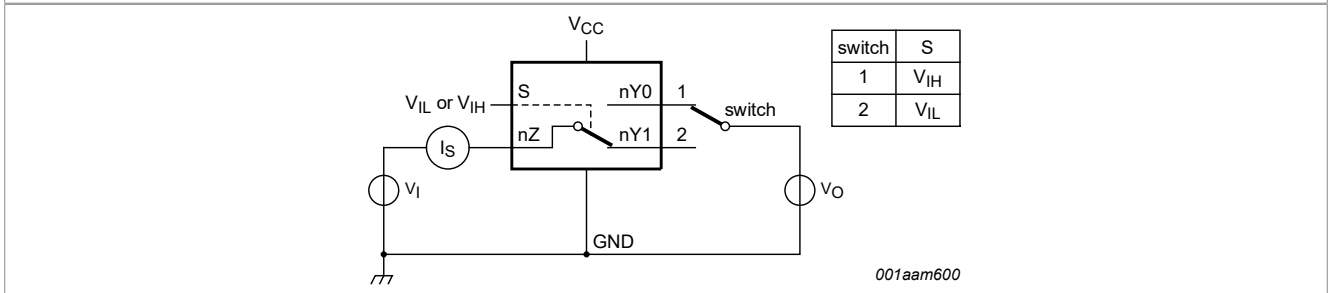
Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
		V _{CC} = 3.6 V	-	-	100	-	500	5000	nA
		V _{CC} = 4.3 V	-	-	150	-	800	6000	nA
ΔI _{CC}	additional supply current	V _{SW} = GND or V _{CC}							
		V _I = 2.6 V; V _{CC} = 4.3 V	-	2.0	4.0	-	7	7	μA
		V _I = 2.6 V; V _{CC} = 3.6 V	-	0.35	0.7	-	1	1	μA
		V _I = 1.8 V; V _{CC} = 4.3 V	-	7.0	10.0	-	15	15	μA
		V _I = 1.8 V; V _{CC} = 3.6 V	-	2.5	4.0	-	5	5	μA
		V _I = 1.8 V; V _{CC} = 2.5 V	-	50	200	-	300	500	nA
C _I	input capacitance		-	1	-	-	-	-	pF
C _{S(OFF)}	OFF-state capacitance	supply path switch	-	35	-	-	-	-	pF
		data path switch	-	3	-	-	-	-	pF
C _{S(ON)}	ON-state capacitance	supply path switch	-	130	-	-	-	-	pF
		data path switch	-	16	-	-	-	-	pF

10.1 Test circuits



V_I = 0.3 V or V_{CC} - 0.3 V; V_O = V_{CC} - 0.3 V or 0.3 V.

Figure 5. Test circuit for measuring OFF-state leakage current



V_I = 0.3 V or V_{CC} - 0.3 V; V_O = V_{CC} - 0.3 V or 0.3 V.

Figure 6. Test circuit for measuring ON-state leakage current

10.2 ON resistance

Table 8. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for graphs see Figure 8 to Figure 13.

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
Supply path switch								
R _{ON}	ON resistance	V _I = GND to V _{CC} ; I _{SW} = 100 mA; see Figure 7						
		V _{CC} = 1.8 V; V _{SW} = 0 V, 1.8 V	-	0.5	0.75	-	0.85	Ω
		V _{CC} = 2.7 V; V _{SW} = 0 V, 2.3 V	-	0.45	0.7	-	0.8	Ω
ΔR _{ON}	ON resistance mismatch between channels	V _I = GND to V _{CC} ; I _{SW} = 100 mA ^[2]						
		V _{CC} = 2.7 V; V _{SW} = 0 V	-	0.1	-	-	-	Ω
Data path switches								
R _{ON}	ON resistance	V _I = GND to V _{CC} ; I _{SW} = 20 mA; see Figure 7						
		V _{CC} = 1.8 V; V _{SW} = 0 V, 1.8 V	-	7.0	10.0	-	11.0	Ω
		V _{CC} = 2.7 V; V _{SW} = 0 V, 2.3 V	-	6.0	9.5	-	10.5	Ω
ΔR _{ON}	ON resistance mismatch between channels	V _I = GND to V _{CC} ; I _{SW} = 20 mA ^[2]						
		V _{CC} = 2.7 V; V _{SW} = 0 V	-	0.2	-	-	-	Ω

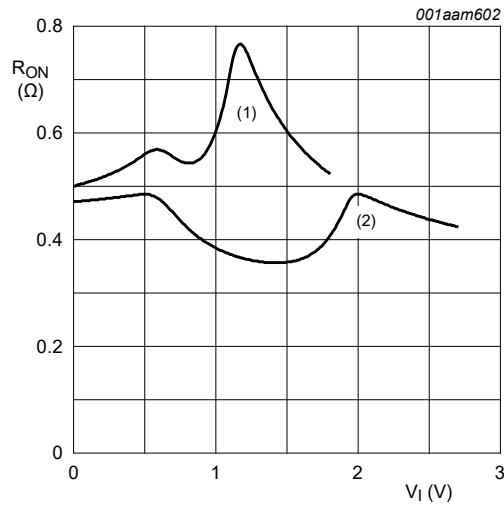
[1] Typical values are measured at T_{amb} = 25 °C.
 [2] Measured at identical V_{CC}, temperature and input voltage.

10.3 ON resistance test circuit and graphs

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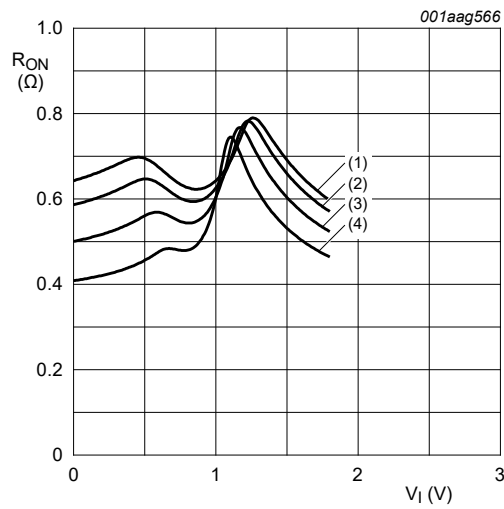
$R_{ON} = V_{SW} / I_{SW}$.

Figure 7. Test circuit for measuring ON resistance



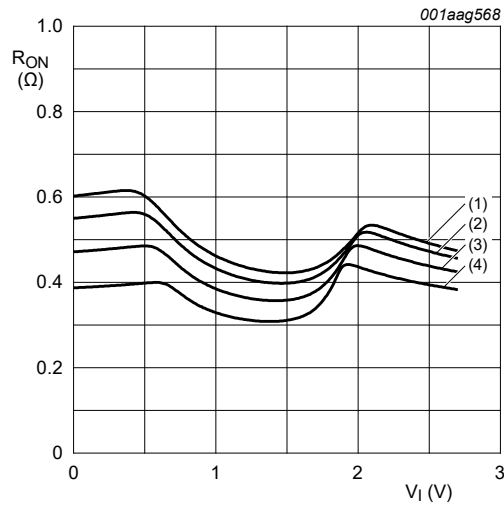
- 1. $V_{CC} = 1.8\text{ V}$.
- 2. $V_{CC} = 2.7\text{ V}$.

Figure 8. Typical ON resistance as a function of input voltage (supply path switch)



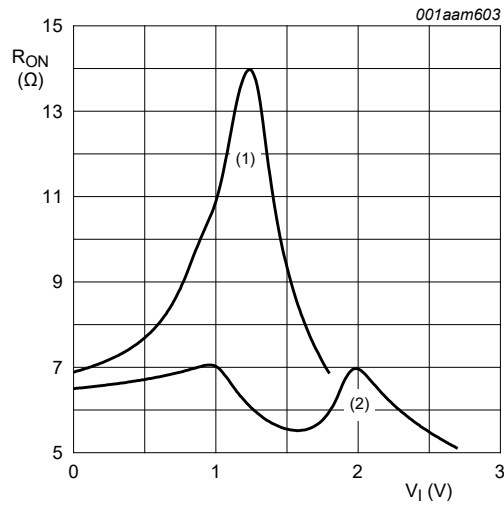
- 1. $T_{amb} = 125\text{ °C}$.
- 2. $T_{amb} = 85\text{ °C}$.
- 3. $T_{amb} = 25\text{ °C}$.
- 4. $T_{amb} = -40\text{ °C}$.

Figure 9. ON resistance as a function of input voltage; $V_{CC} = 1.8\text{ V}$ (supply path switch)



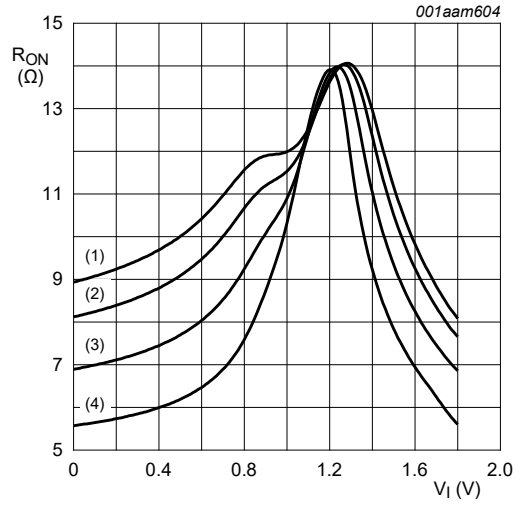
1. $T_{amb} = 125\text{ }^{\circ}\text{C}$.
2. $T_{amb} = 85\text{ }^{\circ}\text{C}$.
3. $T_{amb} = 25\text{ }^{\circ}\text{C}$.
4. $T_{amb} = -40\text{ }^{\circ}\text{C}$.

Figure 10. ON resistance as a function of input voltage; $V_{CC} = 2.7\text{ V}$ (supply path switch)



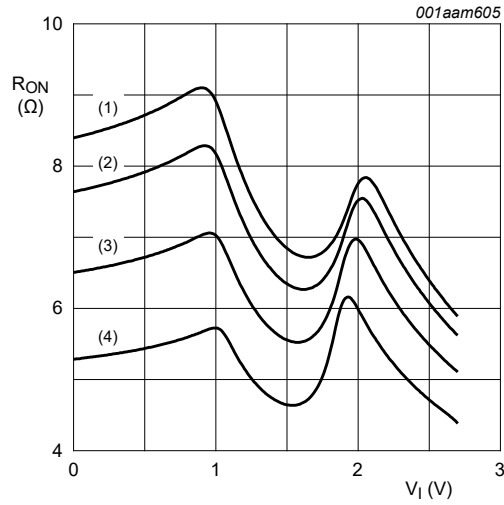
1. $V_{CC} = 1.8\text{ V}$.
2. $V_{CC} = 2.7\text{ V}$.

Figure 11. Typical ON resistance as a function of input voltage (data path switch)



- 1. T_{amb} = 125 °C.
- 2. T_{amb} = 85 °C.
- 3. T_{amb} = 25 °C.
- 4. T_{amb} = -40 °C.

Figure 12. ON resistance as a function of input voltage; V_{CC} = 1.8 V (data path switch)



- 1. T_{amb} = 125 °C.
- 2. T_{amb} = 85 °C.
- 3. T_{amb} = 25 °C.
- 4. T_{amb} = -40 °C.

Figure 13. ON resistance as a function of input voltage; V_{CC} = 2.7 V (data path switch)

11 Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see [Figure 16](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
Supply path switch									
t _{en}	enable time	S to 1Z or 1Y0, 1Y1; see Figure 14							
		V _{CC} = 1.4 V to 1.6 V	-	41	90	-	120	120	ns
		V _{CC} = 1.65 V to 1.95 V	-	30	70	-	80	90	ns
		V _{CC} = 2.3 V to 2.7 V	-	20	45	-	50	55	ns
		V _{CC} = 2.7 V to 3.6 V	-	19	40	-	45	50	ns
		V _{CC} = 3.6 V to 4.3 V	-	19	40	-	45	50	ns
t _{dis}	disable time	S to 1Z or 1Y0, 1Y1; see Figure 14							
		V _{CC} = 1.4 V to 1.6 V	-	24	70	-	80	90	ns
		V _{CC} = 1.65 V to 1.95 V	-	15	55	-	60	65	ns
		V _{CC} = 2.3 V to 2.7 V	-	9	25	-	30	35	ns
		V _{CC} = 2.7 V to 3.6 V	-	8	20	-	25	30	ns
		V _{CC} = 3.6 V to 4.3 V	-	8	20	-	25	30	ns
t _{b-m}	break-before-make time	see Figure 15	[2]						
		V _{CC} = 1.4 V to 1.6 V	-	20	-	9	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	17	-	7	-	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	13	-	4	-	-	ns
		V _{CC} = 2.7 V to 3.6 V	-	11	-	3	-	-	ns
		V _{CC} = 3.6 V to 4.3 V	-	11	-	2	-	-	ns
Data path switch									
t _{en}	enable time	S to nZ or nYn; see Figure 14							
		V _{CC} = 1.4 V to 1.6 V	-	40	90	-	120	120	ns
		V _{CC} = 1.65 V to 1.95 V	-	29	70	-	80	90	ns
		V _{CC} = 2.3 V to 2.7 V	-	20	45	-	50	55	ns
		V _{CC} = 2.7 V to 3.6 V	-	19	40	-	45	50	ns
		V _{CC} = 3.6 V to 4.3 V	-	19	40	-	45	50	ns
t _{dis}	disable time	S to nZ or nYn; see Figure 14							

Table 9. Dynamic characteristics...continued

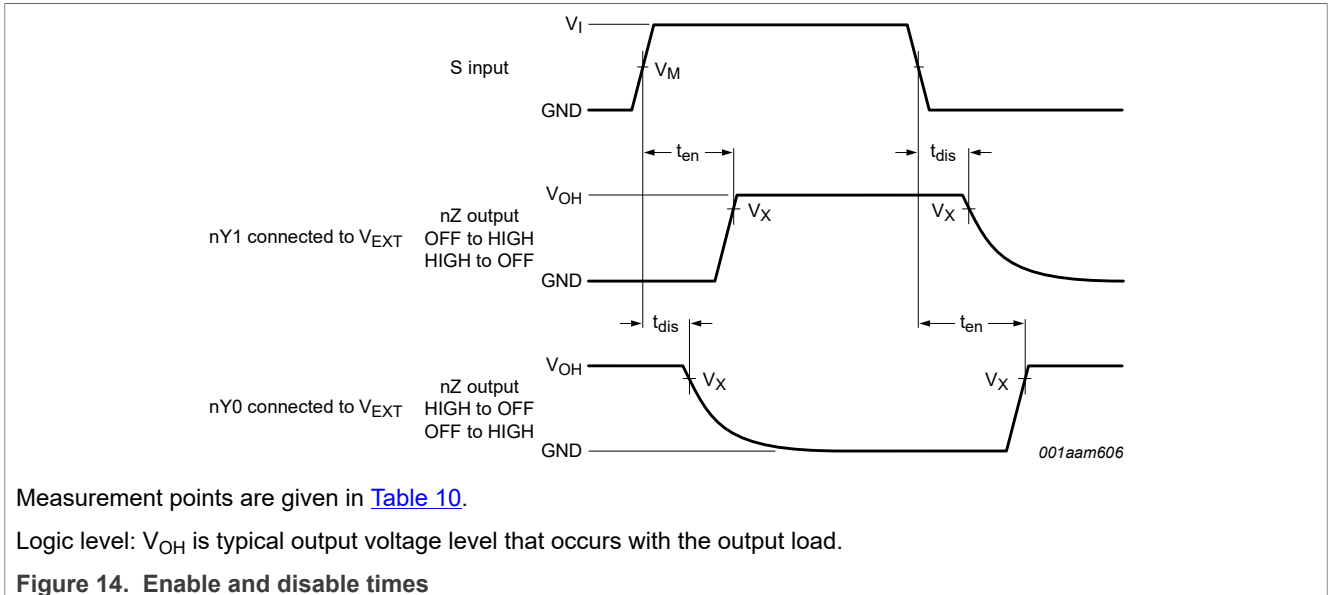
At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see Figure 16.

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
		V _{CC} = 1.4 V to 1.6 V	-	21	70	-	80	90	ns
		V _{CC} = 1.65 V to 1.95 V	-	13	55	-	60	65	ns
		V _{CC} = 2.3 V to 2.7 V	-	8	25	-	30	35	ns
		V _{CC} = 2.7 V to 3.6 V	-	7	20	-	25	30	ns
		V _{CC} = 3.6 V to 4.3 V	-	7	20	-	25	30	ns
t _{b-m}	break-before-make time	see Figure 15	[2]						
		V _{CC} = 1.4 V to 1.6 V	-	23	-	9	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	19	-	7	-	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	15	-	4	-	-	ns
		V _{CC} = 2.7 V to 3.6 V	-	13	-	3	-	-	ns
		V _{CC} = 3.6 V to 4.3 V	-	12	-	2	-	-	ns

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.5 V, 1.8 V, 2.5 V, 3.3 V and 4.3 V respectively.

[2] Break-before-make guaranteed by design.

11.1 Waveform and test circuits



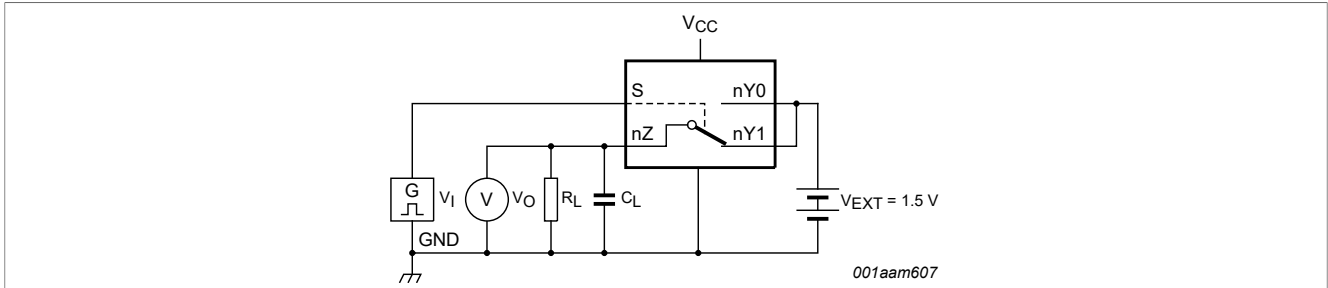
Measurement points are given in Table 10.

Logic level: V_{OH} is typical output voltage level that occurs with the output load.

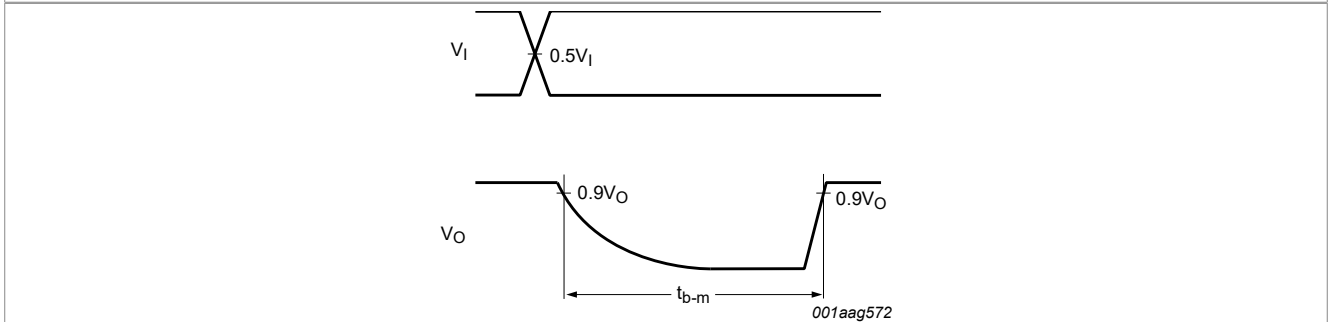
Figure 14. Enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output
V _{CC}	V _M	V _X
1.4 V to 4.3 V	0.5V _{CC}	0.9V _{OH}

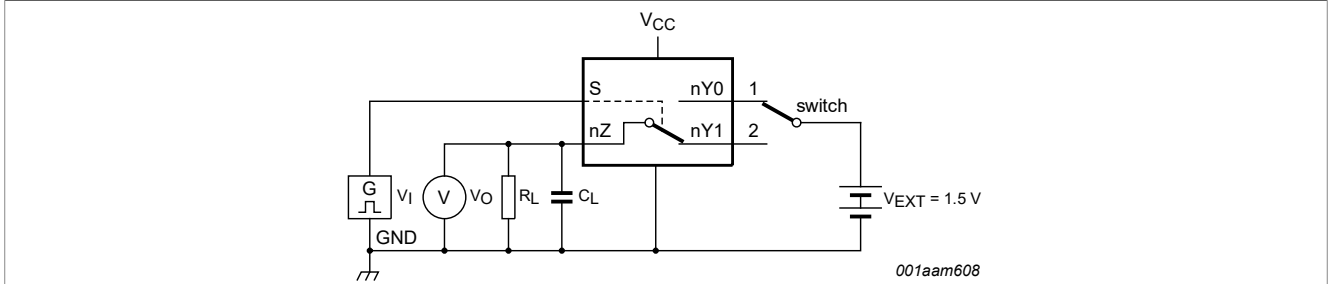


a. Test circuit



b. Input and output measurement points

Figure 15. Test circuit for measuring break-before-make timing



Test data is given in [Table 11](#).

Definitions test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

V_{EXT} = External voltage for measuring switching times.

Figure 16. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Input		Load	
V_{CC}	V_1	t_r, t_f	C_L	R_L
1.4 V to 4.3 V	V_{CC}	≤ 2.5 ns	35 pF	50 Ω

11.2 Additional dynamic characteristics

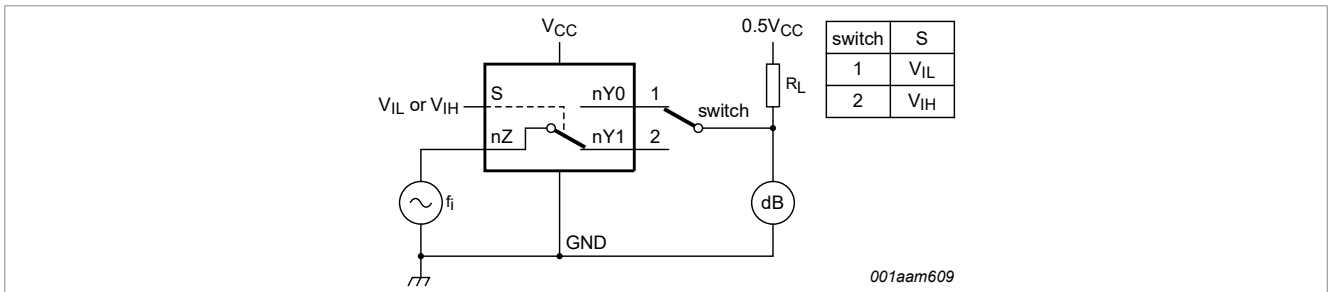
Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $V_I = GND$ or V_{CC} (unless otherwise specified); $t_r = t_f \leq 2.5$ ns; $T_{amb} = 25$ °C.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Data path switch						
$f_{(-3dB)}$	-3 dB frequency response	$R_L = 50 \Omega$; see Figure 17	[1]			
		$V_{CC} = 2.7$ V to 3.6 V		-	330	-
α_{iso}	isolation (OFF-state)	$f_i = 10$ MHz; $R_L = 50 \Omega$; see Figure 18	[1]			
		$V_{CC} = 2.7$ V to 3.6 V		-	-60	-
Xtalk	crosstalk	between switches; $f_i = 10$ MHz; $R_L = 50 \Omega$; see Figure 19	[1]			
		$V_{CC} = 2.7$ V to 3.6 V		-	-60	-
Q_{inj}	charge injection	$f_i = 1$ MHz; $C_L = 0.1$ nF; $R_L = 1$ M Ω ; $V_{gen} = 0$ V; $R_{gen} = 0 \Omega$; see Figure 20				
		$V_{CC} = 2.7$ V to 3.6 V		-	10	-

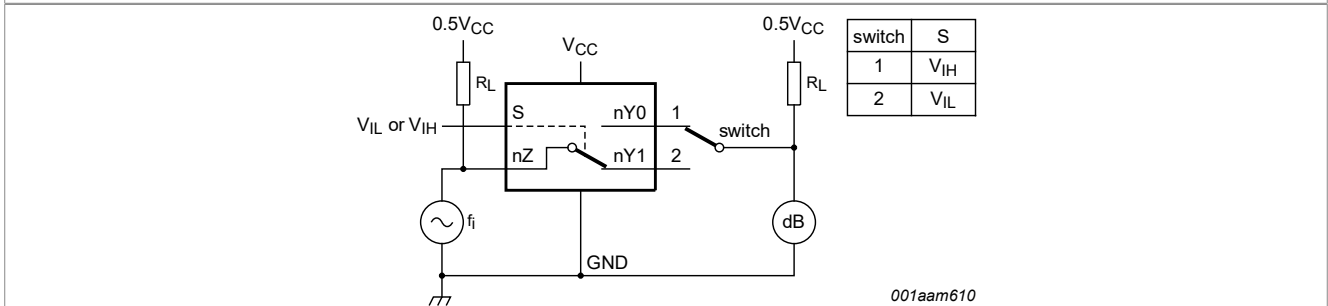
[1] f_i is biased at $0.5V_{CC}$.

11.3 Test circuits



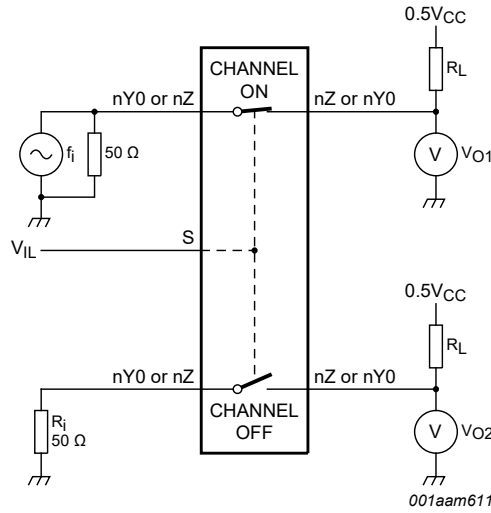
Adjust f_i voltage to obtain 0 dBm level at output. Increase f_i frequency until dB meter reads -3 dB.

Figure 17. Test circuit for measuring the frequency response when channel is in ON-state



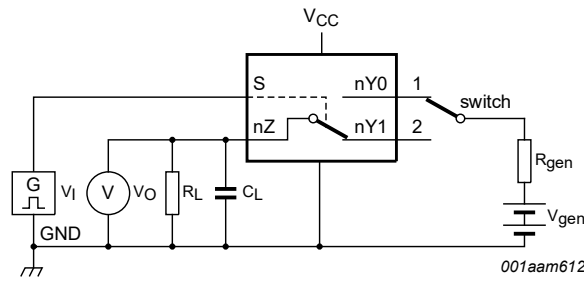
Adjust f_i voltage to obtain 0 dBm level at input.

Figure 18. Test circuit for measuring isolation (OFF-state)

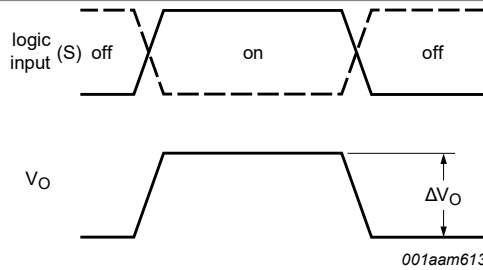


$20 \log_{10} (V_{O2} / V_{O1})$ or $20 \log_{10} (V_{O1} / V_{O2})$.

Figure 19. Test circuit for measuring crosstalk between switches



a. Test circuit



Definition: $Q_{inj} = \Delta V_o \times C_L$.

ΔV_o = output voltage variation.

R_{gen} = generator resistance.

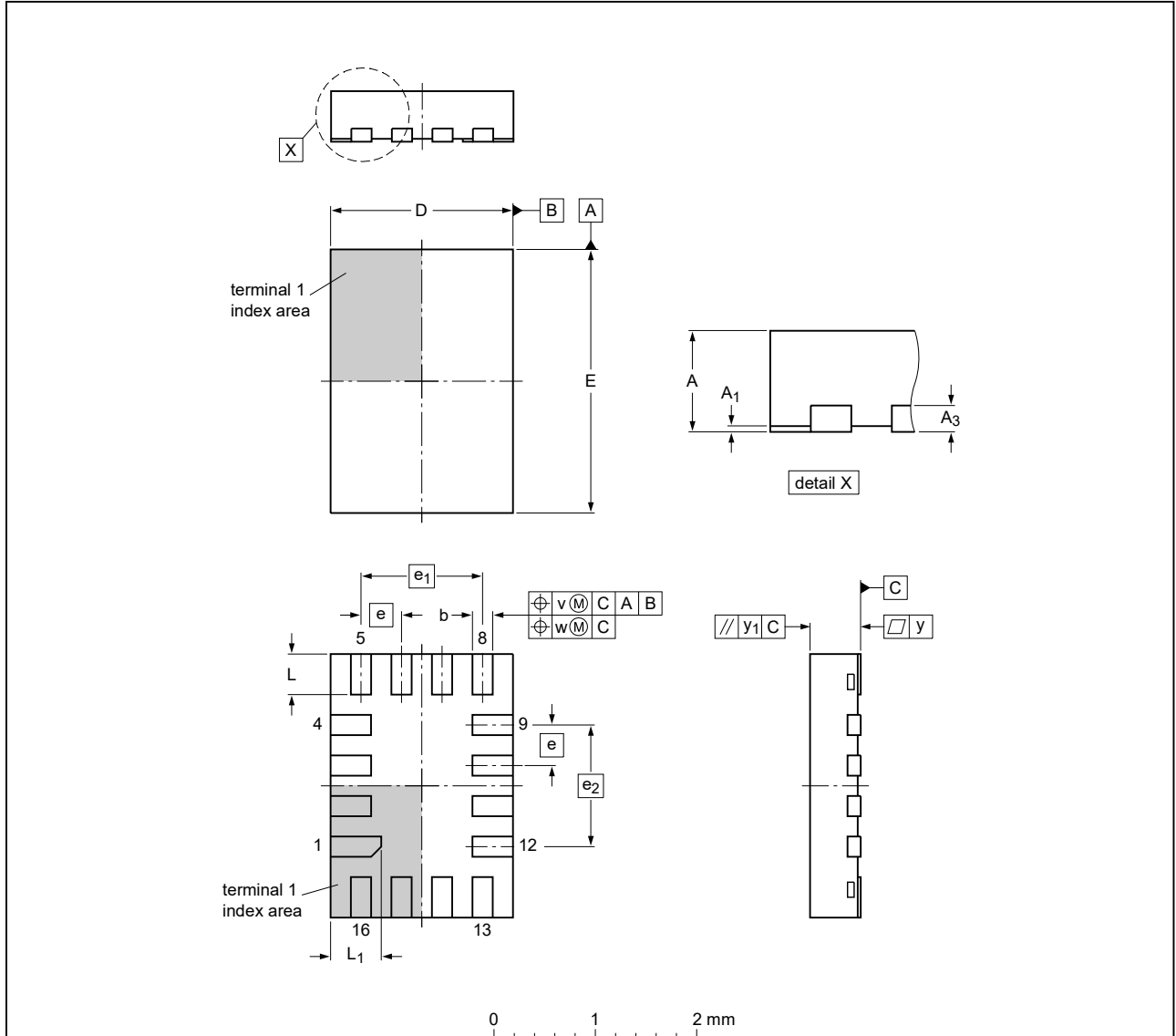
V_{gen} = generator voltage.

b. Input and output pulse definitions

Figure 20. Test circuit for measuring charge injection

XQFN16: plastic, extremely thin quad flat package; no leads;
16 terminals; body 1.80 x 2.60 x 0.50 mm

SOT1161-1



Dimensions

Unit ⁽¹⁾	A	A ₁	A ₃	b	D	E	e	e ₁	e ₂	L	L ₁	v	w	y	y ₁
max	0.5	0.05		0.25	1.9	2.7				0.45	0.55				
mm nom			0.127	0.20	1.8	2.6	0.4	1.2	1.2	0.40	0.50	0.1	0.05	0.05	0.05
min		0.00		0.15	1.7	2.5				0.35	0.45				

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

sot1161-1_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1161-1	---	---	---			09-12-28 09-12-29

Figure 22. Package outline SOT1161-1 (XQFN16)

13 Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
PDA	Personal Digital Assistant
TTL	Transistor-Transistor Logic

14 Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3DV2567 v.2.1	20231004	Product data sheet	-	NX3DV2567 v.2
Modifications:	• Replaced SOT1039-1 with SOT1039-2.			
NX3DV2567 v.2	20111109	Product data sheet	-	NX3DV2567 v.1
NX3DV2567 v.1	20100928	Product data sheet	-	-

15 Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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